AT005SP020EASA

P-Channel Enhancement Mode MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
-20V	40mΩ@-4.5V	-5A
	70mΩ@-2.5V	

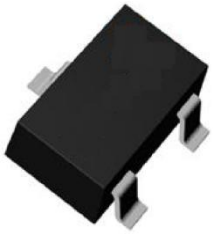
Feature

- Split gate trench MOSFET technology
- Extremely low switching loss
- Excellent stability and uniformity
- Low $R_{DS(on)}$ & FOM

Application

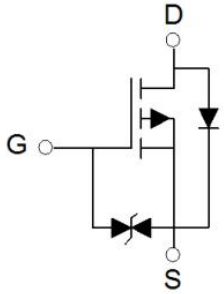
- power management
- Portable equipment

Package

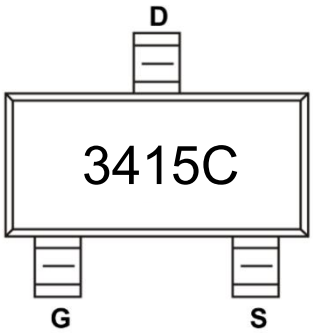


SOT-23

Circuit diagram



Marking



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Absolute maximum ratings (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	±10	V
Continuous Drain Current	I_D	-5	A
Continuous Drain Current (T_A=100℃)	I_D (100℃)	-3.2	A
Pulsed Drain Current[1)]	I_{DM}	-30	A
Power Dissipation[2)]	P_D	1	W
Thermal Resistance Junction to Ambient[3)]	$R_{\theta JA}$	125	℃/W
Operating Junction Temperature	T_J	-55 ~ +150	℃
Storage Temperature	T_{STG}	-55 ~ +150	℃

Electrical characteristics (T_J=25 °C unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} =0V, I_D =-250μA	-20			V
Zero gate voltage drain current	I_{DSS}	V_{DS} =-20V, V_{GS} =0V			-1	μA
Gate-body leakage current	I_{GSS}	V_{DS} =0V, V_{GS} =±10V			±10	μA
Gate threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =-250μA	-0.55	-0.85	-1.25	V
Drain-source on-resistance	$R_{DS(on)}$	V_{GS} =-4.5V, I_D =-5A		28	40	mΩ
		V_{GS} =-2.5V, I_D =-4A		50	70	
Dynamic characteristics[4)]						
Input Capacitance	C_{iss}	V_{DS} =-10V, V_{GS} =0V, f =1MHz		540		pF
Output Capacitance	C_{oss}			120		
Reverse Transfer Capacitance	C_{rss}			100		
Total Gate Charge	Q_g	V_{DS} =-10V, V_{GS} =-10V, I_D =-5A		13		nC
Gate-Source Charge	Q_{gs}			2		
Gate-Drain Charge	Q_{gd}			2		
Turn-on delay time	$t_{d(on)}$	V_{DS} =-10V, V_{GS} =-10V, I_D =-5A R_G =2.2Ω		5		nS
Turn-on rise time	t_r			47		
Turn-off delay time	$t_{d(off)}$			52		
Turn-off fall time	t_f			69		
Source-Drain Diode characteristics						
Diode Forward Current	I_S				-5	A
Diode Forward voltage	V_{SD}	V_{GS} =0V, I_S =-5A			-1.2	V
Reverse Recovery Time	T_{rr}	I_F =-5A, di/dt =-100A/us		20		nS
Reverse Recovery Charge	Q_{rr}			2.5		nC

Notes:

1) Repetitive rating; pulse width limited by max. junction temperature.

2) P_d is based on max. junction temperature, using junction-case and junction-ambient thermal resistance.

3) The value of $R_{\theta JA}$ is measured with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in the still air environment with T_A=25℃. The maximum allowed junction temperature of 150℃. The value in any given application depends on the user's specific board design.

4) Guaranteed by design, not subject to production testing.

Typical Characteristics

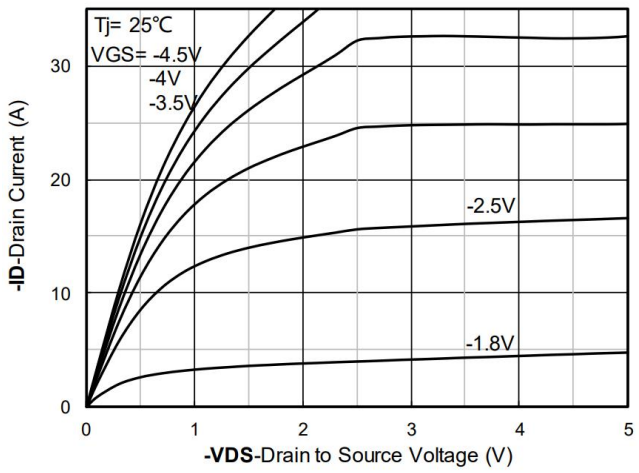


Figure 1. Output Characteristics

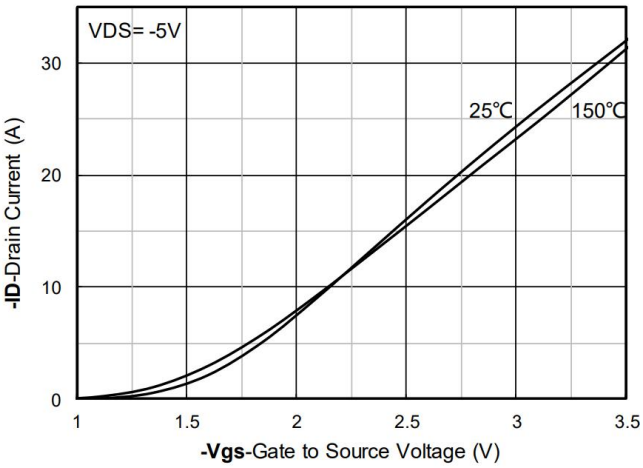


Figure 2. Transfer Characteristics

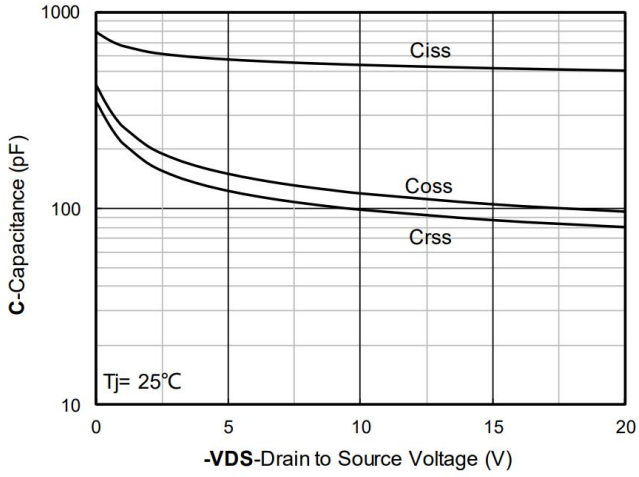


Figure 3. Capacitance Characteristics

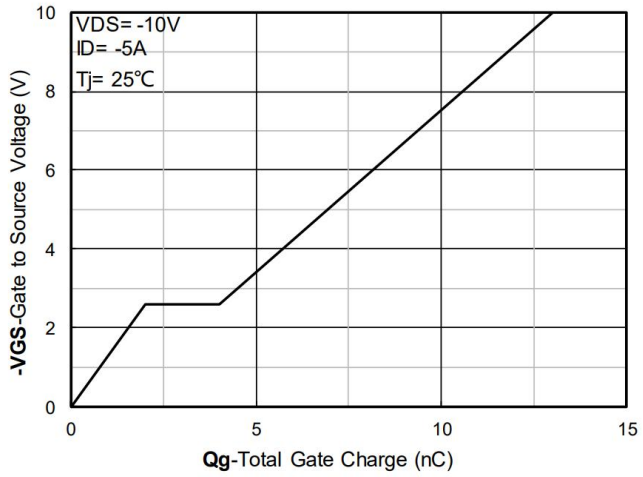


Figure 4. Gate Charge

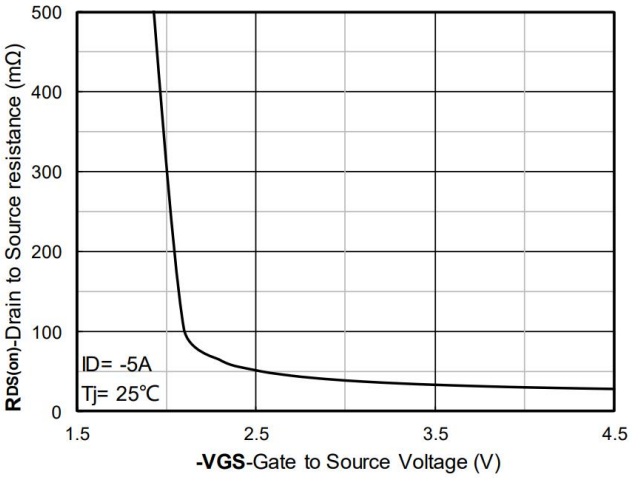


Figure 5. On-Resistance vs Gate to Source Voltage

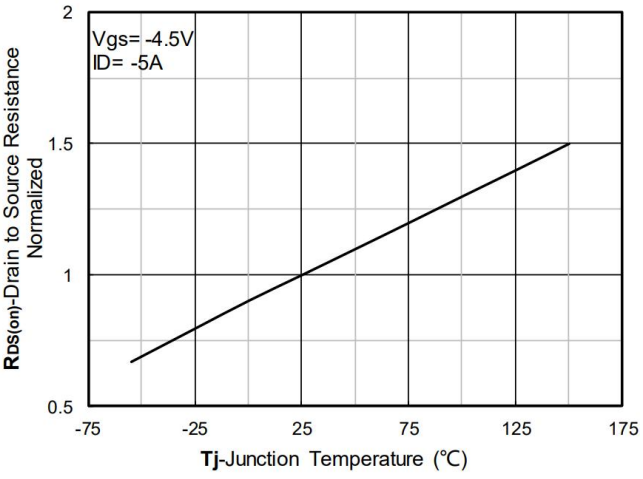


Figure 6. Normalized On-Resistance

Typical Characteristics

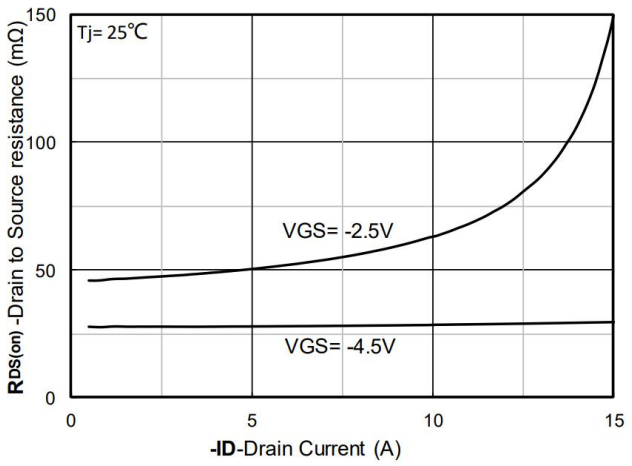


Figure 7. $R_{DS(on)}$ VS Drain Current

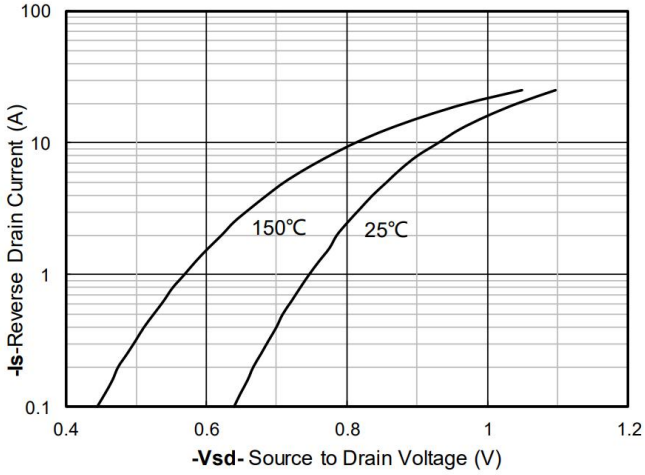


Figure 8. Forward characteristics of reverse diode

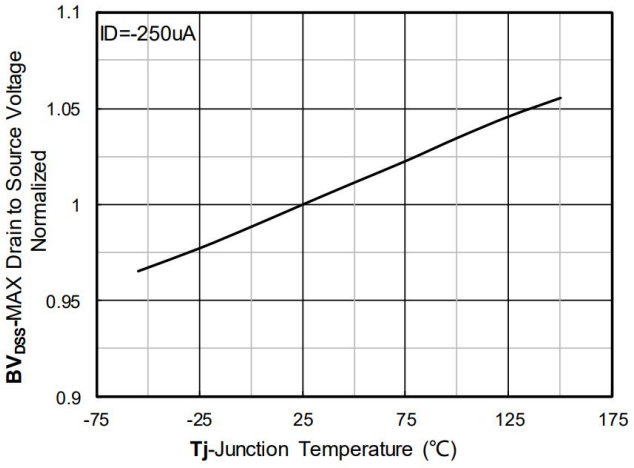


Figure 9. Normalized breakdown voltage

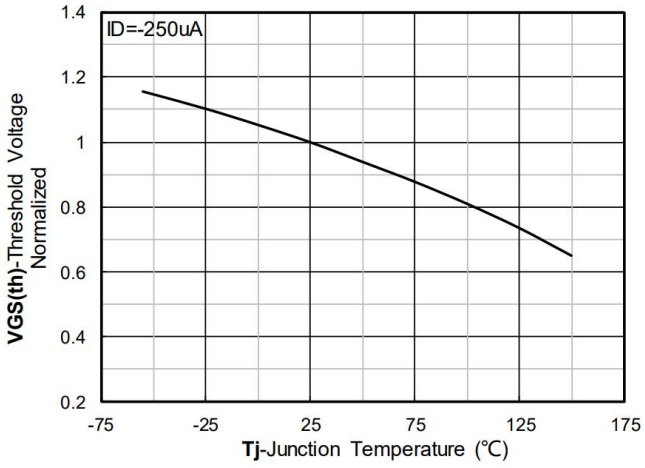


Figure 10. Normalized Threshold voltage

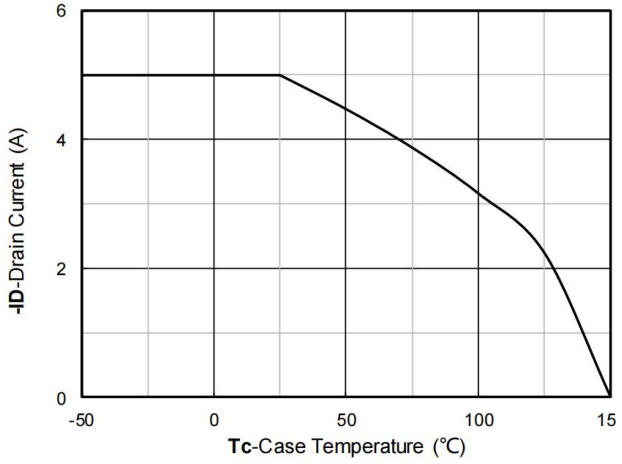


Figure 11. Current dissipation

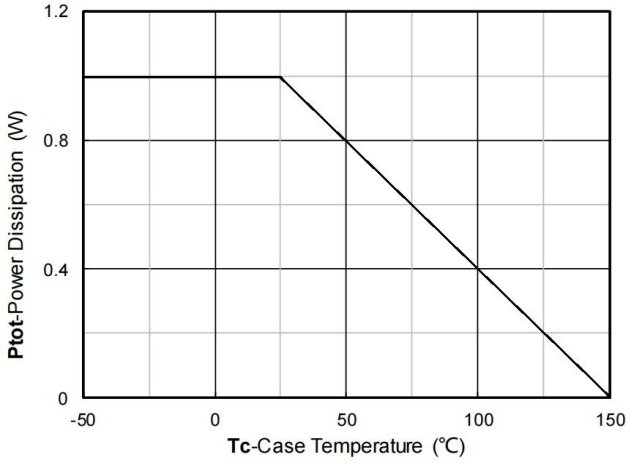
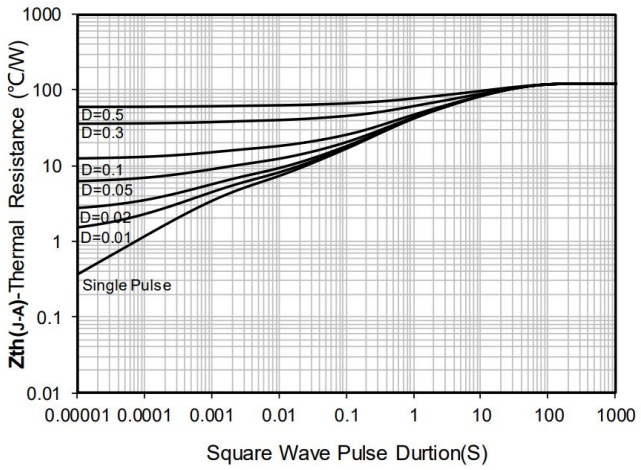
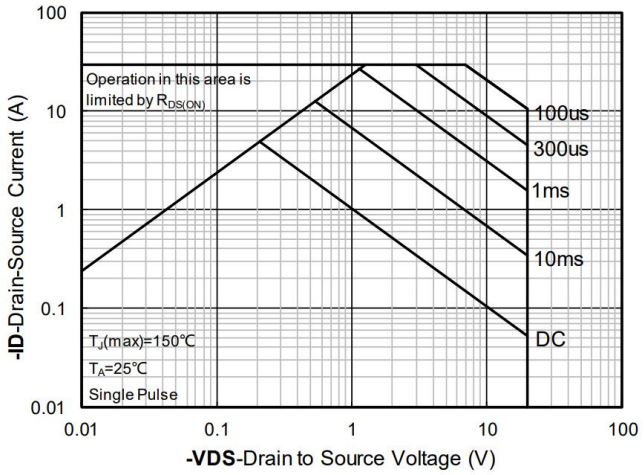


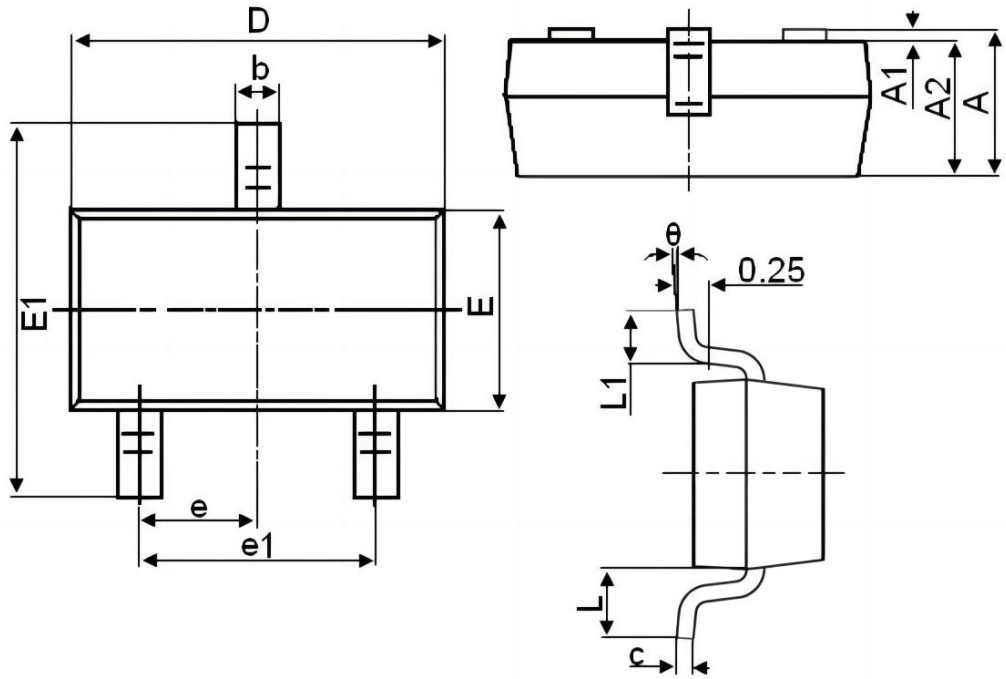
Figure 12. Power dissipation

Typical Characteristics





SOT-23 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°